

PATENT  
W&B Ref. No. : INF 2070-US  
Atty. Dkt. No. INFN/WB0041

**IN THE ABSTRACT:**

Please replace the Abstract with the following amended Abstract:

~~The invention relates to a~~ A dynamic memory cell which can be selected by means of a selection signal and the content of which can be read out by means of a bit line pair with a first and a second bit line, having a storage capacitor and a first and a second selection transistor, in which case, depending on the selection signal, a first terminal of the storage capacitor can be connected to the first bit line via the first selection transistor and a second terminal of the storage capacitor can be connected to the second bit line via the second selection transistor, is provided.